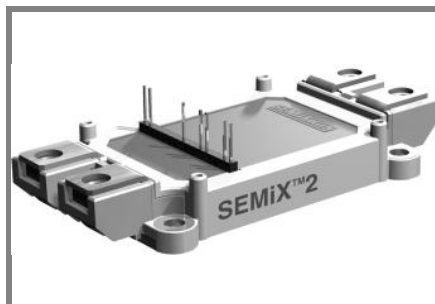


SEMiX 452GB176HD



SEMiX® 2

Trench IGBT Modules

SEMiX 452GB176HD

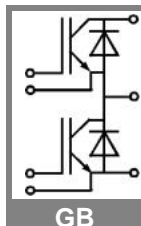
Target Data

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

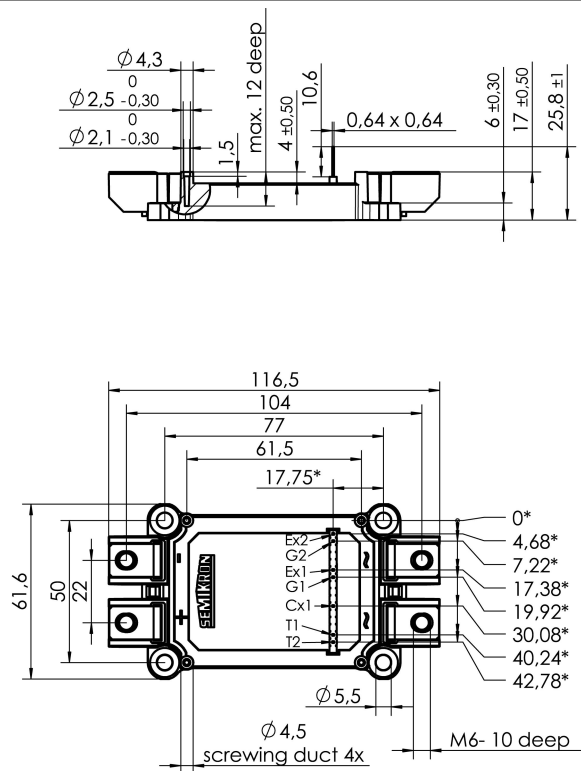
Typical Applications

- AC inverter drives
- UPS
- Electronic welders



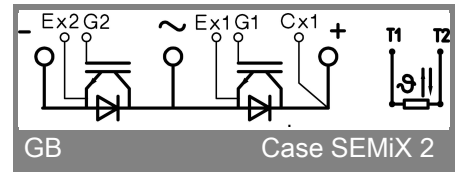
Absolute Maximum Ratings		$T_{case} = 25^{\circ}C$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1700	V
I_C	$T_c = 25 (80)^{\circ}C$	450 (290)	A
I_{CRM}	$t_p = 1 \text{ ms}$	600	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^{\circ}C$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25 (80)^{\circ}C$	300 (200)	A
I_{FRM}	$t_p = 1 \text{ ms}$	600	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 25^{\circ}C$	2000	A

Characteristics		T _{case} = 25°C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 12 mA	5,2	5,8	6,4	V
I _{CES}	V _{GE} = 0, V _{CE} = V _{CES} , T _j = 25 (125) °C			2,4	mA
V _{CE(TO)}	T _j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V
r _{CE}	V _{GE} = 15 V, T _j = 25 (125) °C		3,3 (5,2)	4,2 (6)	mΩ
V _{CE(sat)}	I _{Cnom} = 300 A, V _{GE} = 15 V, T _j = 25 (125) °C, chip level		2 (2,45)	2,45 (2,9)	V
C _{ies}	under following conditions		20		nF
C _{oes}	V _{GE} = 0, V _{CE} = 25 V, f = 1 MHz		1,1		nF
C _{res}			0,9		nF
L _{CE}			18		nH
R _{CC'+EE'}	terminal-chip, T _c = 25 (125) °C				mΩ
t _{d(on)} /t _r	V _{CC} = 1200 V, I _{Cnom} = 300 A				ns
t _{d(off)} /t _f	V _{GE} = ± 15 V				ns
E _{on} (E _{off})	R _{Gon} = R _{Goff} = Ω, T _j = 125 °C		200 (100)		mJ
Inverse diode					
V _F = V _{EC}	I _{Fnom} = 300 A; V _{GE} = 0 V; T _j = 25 (125) °C, chip level		2 (2,1)	2,2 (2,3)	V
V _(TO)	T _j = 25 (125) °C		1,1 (0,9)	1,3 (1,1)	V
r _T	T _j = 25 (125) °C		3 (4)	3 (4)	mΩ
I _{RRM}	I _{Fnom} = 300 A; T _j = 25 (125) °C				A
Q _{rr}	di/dt = A/μs				μC
E _{rr}	V _{GE} = 0 V				mJ
Thermal characteristics					
R _{th(j-c)}	per IGBT			0,07	K/W
R _{th(j-c)D}	per Inverse Diode			0,17	K/W
R _{th(j-c)FD}	per FWD				K/W
R _{th(c-s)}	per module		0,045		K/W
Temperature sensor					
R ₂₅	T _c = 25 °C		5 ±5%		kΩ
B _{25/85}	R ₂ =R ₁ exp[B(1/T ₂ -1/T ₁)] ; T[K];B		3420		K
Mechanical data					
M _s /M _t	to heatsink (M5) / for terminals (M6)	3/2,5		5 /5	Nm
w			236		g



*= all measures with $\phi 0,5$

Case SEMiX 2



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.